Customer No.: 31561 Application No.: 10/710,818 Docket No.: 14217-US-PA-X

REMARKS

Present Status of the Application

Claims 1-10 are rejected under 35 U.S.C. 103(a) as being unpatentable over the AAPA of this application in combination with Shokouhi et al. (US patent 6,249,458).

Applicant has amended claim 1 to more clearly define the present invention. After entry of the foregoing amendments, claims 1-10 remain pending in the present application, and reconsideration of those claims is respectfully requested.

Discussion of Office Action Rejections

The Advisory Action stated that since pending claims recite "comprising", the claimed invention does not exclude inclusion of other element or steps that are recited.

Currently, claim 1 is amended as below:

Claim 1. An electrostatic discharge (ESD) protection device, comprising: an ESD protection circuit, comprising:

at least a diode connected in series between a first voltage and a pad; and at least an ESD component connected in series between a second voltage and a pad, wherein each of the at least an ESD component is composed of a deep N-well region formed in a P-type substrate, a triple P-well formed in the deep N-well region, and a highly doped N-type (N+) region and a highly doped P-type (P+) region formed in the triple P-well region.

The device of Fig. 7 disclosed by Shokouhi et al. is a triple P-well resistor including two

P-doped regions 731, 733 in the triple P-well 730 formed in the deep N-well 720 that is formed
in a P-substrate 710, and the deep N-well 720 is biased by a system voltage (Vcc) and the P-

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substrate 710 is grounded, thereby reverse biasing the central P-well region to limit leakage

current from the P-well region. However, the device in claim 1 is each of the ESD components

including a highly doped N-type region and a highly doped P-type region formed in a triple P-

well located in a deep N-well region that is formed in a P-type substrate. Apparent the structure

of the device disclosed by Shokouhi et al. are much different from the ESD component of claim

1 in structure. Thus, even combined with each other, the AAPA and Shokouhi '458 do not teach

or suggest all of the limitations, as set forth in claim 1. MPEP §2143.03

The Advisory Action pointed out the motivation for combing the teachings of Shokouhi into

the device of AAPA is to prevent leakage current. Further, it is submitted that since the

applicant claims combination, this must be an evidence of success for the combination.

Applicant agrees that the combination of the teachings of Shokouhi into the device of

AAPA is to prevent leakage current. However, the design of the device in the present invention

is for reducing the parasitic capacitance and substrate noise of the ESD device but not to

prevent leakage current. Therefore, the mere fact that references combined or modified does not

render the resultant combination obvious unless the prior art also suggests the desirability of the

combination. In re Mills, 916 F.2d 680, 16 USPQ2d 1430 (Fed. Cir. 1990). To one of ordinary

skill in the art, with mere a teaching given by Shokouhi of preventing leakage current, Shokouhi

'458 teaches, if any, away from combining "forming a device in a triple P-well located in a deep

N-well region that is formed in a P-type substrate" with the AAPA. Therefore, Applicants

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submit that the present invention as set forth in claim 1 should not be considered as obvious over

the AAPA in view of Shokouhi '458.

Further, the point of argument is not the difference between the advantages of respectively

the present invention and the prior art. The point is there is no teaching or suggestion to make

the claimed combination and the reasonable expectation of success found in the cited references.

Without such teaching or suggestion, the combination between the cited references can not

render the present invention obvious. MPEP §2143.

For at least the foregoing reasons, Applicant respectfully submits that independent claim 1

patently define over the prior art references, and should be allowed. For at least the same reasons,

dependent claims 2-10 patently define over the prior art as a matter of law.

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CONCLUSION

For at least the foregoing reasons, it is believed that the pending claims 1-10 are in proper condition for allowance. If the Examiner believes that a telephone conference would expedite the examination of the above-identified patent application, the Examiner is invited to call the undersigned.

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Respectfully submitted,

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